

Mid-Power LED - 3528 Series

S1W0-2835xx8003-00000000-0P006 (Cool, Neutral, Warm)







Product Brief

Description

- This White Colored surface-mount LED comes in standard package dimension. Package Size: 3.5x2.8x0.7mm
- It has a substrate made up of a molded plastic reflector sitting on top of a lead frame.
- The die is attached within the reflector cavity and the cavity is encapsulated by silicone.
- The package design coupled with careful selection of component materials allow these products to perform with high reliability.

Features and Benefits

- Market Standard 3528 Package Size
- High Color Quality, CRI Min. 80
- · RoHS compliant

Key Applications

- Interior lighting
- General lighting
- · Indoor and outdoor displays
- Architectural / Decorative lighting

Table 1. Product Selection Table

Reference Code	Color	Nominal	Part Number	CRI
Reference Code	Color	ССТ	Fart Number	Min
		6500K	S1W0-2835658003-00000000-0P006	
	Cool White Neutral White	5700K	S1W0-2835578003-00000000-0P006	
		5000K	S1W0-2835508003-00000000-0P006	
		4500K	S1W0-2835458003-00000000-0P006	
STW8A2PD-E1(H)		4000K	S1W0-2835408003-00000000-0P006	80
	Warm	3500K	S1W0-2835358003-00000000-0P006	
		3000K	S1W0-2835308003-00000000-0P006	
	White	2700K	S1W0-2835278003-00000000-0P006	
		2200K	S1W0-2835228003-00000000-0P006	.



Table of Contents

Inde	ex	
•	Product Brief	1
•	Table of Contents	2
•	Performance Characteristics	3
•	Characteristics Graph	5
•	Color Bin Structure	11
•	Mechanical Dimensions	15
•	Recommended Solder Pad	16
•	Reflow Soldering Characteristics	17
•	Emitter Tape & Reel Packaging	18
•	Product Nomenclature	20
•	Handling of Silicone Resin for LEDs	21
•	Precaution For Use	22
•	Company Information	25

Performance Characteristics

Table 2. Product Selection Guide, $I_F = 65mA$, $T_j = 25^{\circ}C$, RH30%

Min. CRI, Ra	Nominal CCT [K] [[]	Min. Flux [lm]	Typ. Luminous Flux Φ _V ^[2] [lm] @65mA	Typ. Luminous Efficacy [lm/W] @65mA	Part Number
	6500	33.9	36.1	203.9	S1W0-2835658003-00000000-0P006
	5700	35.1	36.4	205.8	S1W0-2835578003-00000000-0P006
	5000	35.1	36.9	208.7	S1W0-2835508003-00000000-0P006
	4500	35.1	36.9	208.7	S1W0-2835458003-00000000-0P006
80	4000	35.1	36.9	208.7	S1W0-2835408003-00000000-0P006
	3500	33.9	35.4	199.9	S1W0-2835358003-00000000-0P006
	3000	33.0	35.0	198.1	S1W0-2835308003-00000000-0P006
	2700	33.0	34.0	192.2	S1W0-2835278003-00000000-0P006
	2200	28.5	29.4	167.0	S1W0-2835228003-00000000-0P006

Notes:

- (1) Correlated Color Temperature is derived from the CIE 1931 Chromaticity diagram.
- (2) Seoul Semiconductor maintains a tolerance of $\pm 5\%$ on Flux and power measurements. The luminous Flux was measured at the peak of the spatial pattern which may not be aligned with the mechanical axis of the LED package.



Performance Characteristics

Table 3. Characteristics, I_F=65mA, T_i= 25°C, RH30%

Parameter	Camb ol		Unit			
Parameter	Symbol	Min.	Тур.	Max.	Onit	
Forward Current	I _F	-	65	-	mA	
Forward Voltage	V_{F}	-	2.72	2.76	V	
CRI ^[3]	Ra	80	83	90		
R9	R9	0	8			
Viewing Angle	2Θ _{1/2}	-	120	-	Deg.	
Storage Temperature	T_{stg}	-40	-	85	°C	
Thermal resistance (J to S) [4]	Rθ _{J-S}	-	13	-	°C/W	
ESD Sensitivity(HBM)	-	Class 2 JESD22-A114-E				

Table 4. Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Forward Current	I _F	300	mA
Power Dissipation	P_{D}	1.0	W
Junction Temperature	T _j	125	°C
Operating Temperature	T _{opr}	-40 ~ + 85	°C
Storage Temperature	T _{stg}	-40 ~ + 100	°C

Notes:

- (1) Seoul Semiconductor maintains a tolerance of $\pm 5\%$ on Flux and power measurements.
- (2) Correlated Color Temperature is derived from the CIE 1931 Chromaticity diagram.

Color coordinate : ± 0.005 , CCT $\pm 5\%$ tolerance.

- (3) Tolerance is ± 2.0 on CRI , ± 0.1 on VF measurements.
- (4) Thermal resistance is junction to Solder.
- (5) The products are sensitive to static electricity and must be carefully taken when handling products
- (6) It is recommended to use it in the condition that the reliability is secured within the Max value.
- · Calculated performance values are for reference only.
- · All measurements were made under the standardized environment of Seoul Semiconductor.

Fig 1. Color Spectrum, T_i = 25°C, I_F=65mA

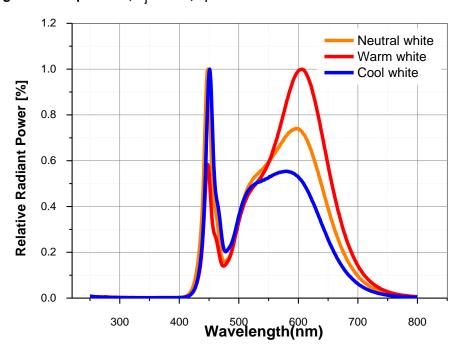


Fig 2. Radiant Pattern, T_i = 25°C, I_F=65mA

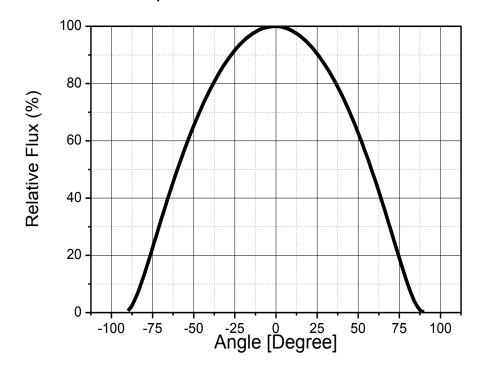


Fig 3. Forward Voltage vs. Forward Current, $T_j = 25^{\circ}C$

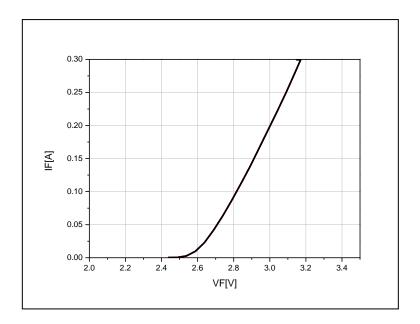
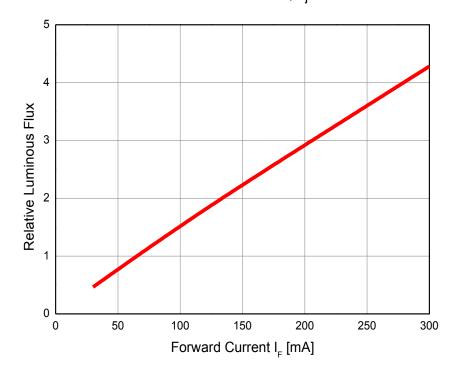


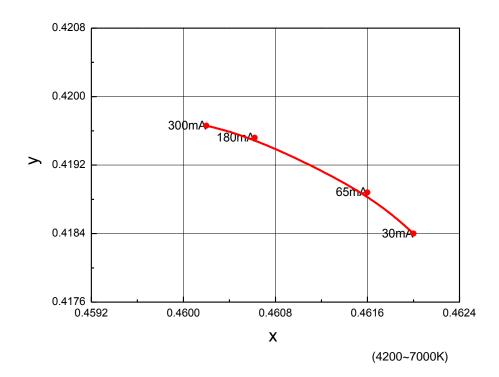
Fig 4. Forward Current vs. Relative Luminous Flux, T_i = 25°C



Characteristics Graph

Fig 5. Forward Current vs. CIE X,Y Shift, $T_j = 25^{\circ}C$

(2600~4200K)



0.3480

> 0.3475

0.3470

0.3465

0.3312

0.3316

0.3320

0.3324

0.3328

X

Fig 6. Junction Temperature vs. Relative Luminous Flux, I_F=65mA

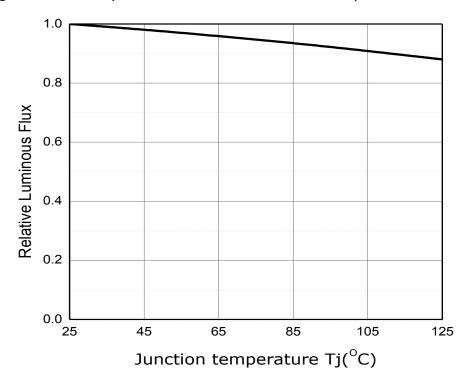


Fig 7. Junction Temperature vs. Relative Forward Voltage, I_F=65mA

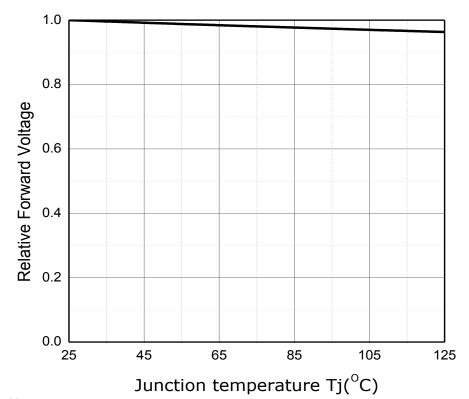
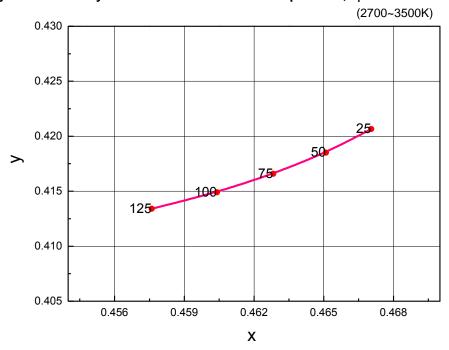
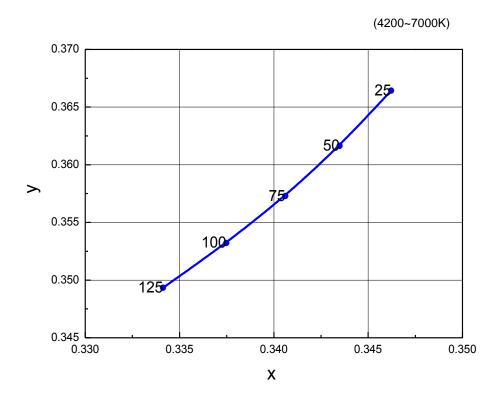
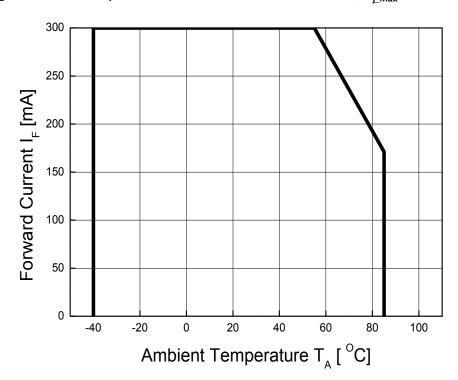




Fig 8. Chromaticity Coordinate vs. Junction Temperature, I_F=65mA









Color Bin Structure

Table 5. Bin Code description, $T_j=25^{\circ}C$, $I_F=65mA$

Part Number	Luminous Flux (lm)			Color	Typical Forward Voltage (V)		
	Bin Code	Min.	Max.	Chromaticity Coordinate	Bin Code	Min.	Max.
	S5	28.5	30.0		Y1L	2.68	2.73
	T0	30.0	31.5	Refer to Page. 12	Y1H	2.73	2.76
	T5	31.5	33.0				
S1W0- 2835xx8003-	U0	33.0	33.9				
00000000- 0P006	U3	33.9	35.1				
0. 300	U7	35.1	36.3				
	V1	36.3	37.2				
	V4	37.2	38.1				

Table 6. Flux rank distribution

Available ranks

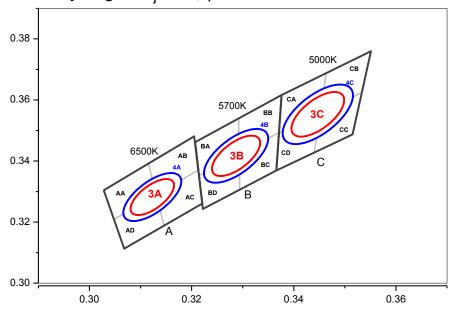
ССТ	CIE	Flux Rank					
6,000 ~ 7,000K	Α	U0	U3	U7	V1	V4	
5,300 – 6,000K	В	U0	U3	U7	V1	V4	
4,700 ~ 5,300K	С	U0	U3	U7	V1	V4	
4,200 ~ 4,700K	D	U0	U3	U7	V1	V4	
3,700 ~ 4,200K	E	U0	U3	U7	V1	V4	
3,200 ~ 3,700K	F	U0	U3	U7	V1	V4	
2,900 ~ 3,200K	G	U0	U3	U7	V1	V4	
2,600 ~ 2,900K	Н	U0	U3	U7	V1	V4	
2,100 ~ 2,300K	K	S5	ТО	T5	-	-	

*Notes:

All measurements were made under the standardized environment of Seoul Semiconductor.
 In order to ensure availability, single color rank will not be orderable.

Color Bin Structure

CIE Chromaticity Diagram T_j =25 $^{\circ}$ C, I_F =65mA



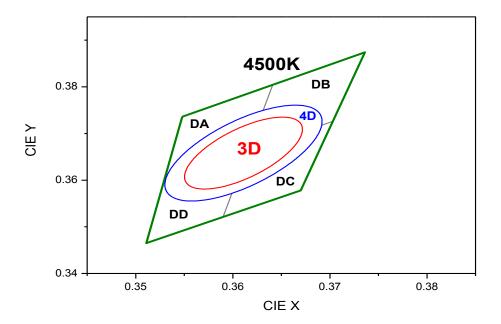
6500	K 3Step	5700	K 3Step	5000K 3Step		
	3A		3B	3C		
Center point	0.3123 : 0.3282	Center point	0.3287 : 0.3417	Center point	0.3447 : 0.3553	
Major Axis a	0.00669	Major Axis a	0.00746	Major Axis a	0.00822	
Minor Axis b	0.00285	Minor Axis b	0.00320	Minor Axis b	0.00354	
Ellipse Rotation Angle	58.57	Ellipse Rotation Angle	59.09	Ellipse Rotation Angle	59.62	

6500	K 4Step	5700	K 4Step	5000K 4Step		
	4A		4B	4C		
Center point	0.3123 : 0.3282	Center point	0.3287 : 0.3417	Center point	0.3447 : 0.3553	
Major Axis a	0.00892	Major Axis a	0.00995	Major Axis a	0.01096	
Minor Axis b	0.00380	Minor Axis b	0.00427	Minor Axis b	0.00472	
Ellipse	58.57	Ellipse	59.09	Ellipse	59.62	
Rotation Angle	00.07	Rotation Angle		Rotation Angle		

Α	A	А	В	Α	С	Α	D
CIE X	CIE Y						
0.3028	0.3304	0.3115	0.3393	0.3131	0.329	0.3048	0.3209
0.3048	0.3209	0.3131	0.329	0.3146	0.3187	0.3068	0.3113
0.3131	0.329	0.3213	0.3371	0.3221	0.3261	0.3146	0.3187
0.3115	0.3393	0.3205	0.3481	0.3213	0.3371	0.3131	0.329
В	A	В	В	В	C	В	D
CIE X	CIE Y						
0.3207	0.3462	0.3292	0.3539	0.3293	0.3423	0.3215	0.3353
0.3215	0.3353	0.3293	0.3423	0.3294	0.3306	0.3222	0.3243
0.3293	0.3423	0.3371	0.3493	0.3366	0.3369	0.3294	0.3306
0.3292	0.3539	0.3376	0.3616	0.3371	0.3493	0.3293	0.3423
С	A	c	В	c	C	C	D
CIE X	CIE Y						
0.3376	0.3616	0.3463	0.3687	0.3452	0.3558	0.3371	0.3493
0.3371	0.3493	0.3452	0.3558	0.344	0.3428	0.3366	0.3369
0.3452	0.3558	0.3533	0.3624	0.3514	0.3487	0.344	0.3428
0.3463	0.3687	0.3551	0.376	0.3533	0.3624	0.3452	0.3558

Color Bin Structure

CIE Chromaticity Diagram T_i=25℃, I_F=65mA



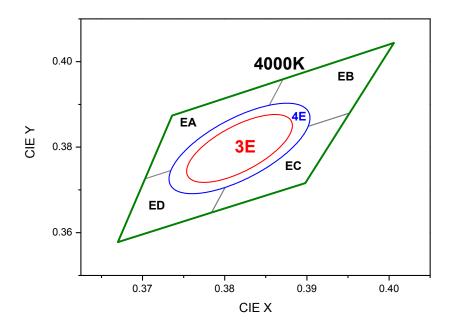
4500K 3Step 3D Center point 0.3611, 0.3658 Major Axis a 0.009 Minor Axis b 0.0039 Ellipse 55 Rotation Angle

4500K 4Step							
4D							
Center point	0.3611, 0.3658						
Major Axis a	0.012						
Minor Axis b	0.0052						
Ellipse Rotation Angle	55						

D)A	D	В	D	С	D	D
CIE X	CIE Y						
0.3548	0.3736	0.3641	0.3804	0.3616	0.3663	0.3530	0.3601
0.3530	0.3601	0.3616	0.3663	0.3590	0.3521	0.3511	0.3465
0.3616	0.3663	0.3703	0.3726	0.3670	0.3578	0.3590	0.3521
0.3641	0.3804	0.3736	0.3874	0.3703	0.3726	0.3616	0.3663

Color Bin Structure

CIE Chromaticity Diagram T_i=25℃, I_F=65mA

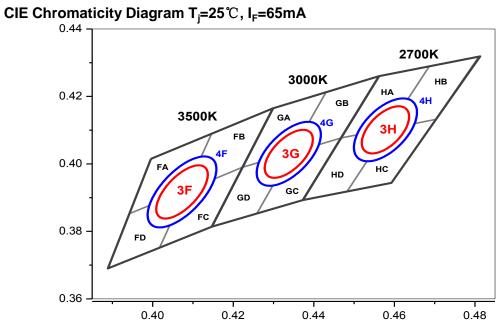


4000K 3Step 3E Center point 0.3818:0.3797 Major Axis a 0.00939 Minor Axis b 0.00402 Ellipse 53.72 Rotation Angle 53.72

4000K 4Step						
4E						
Center point	0.3818 : 0.3797					
Major Axis a	0.01252					
Minor Axis b	0.00536					
Ellipse Rotation Angle	53.72					

E	A	Е	В	Е	С	Е	D
CIE X	CIE Y						
0.3736	0.3874	0.3871	0.3959	0.3828	0.3803	0.3703	0.3726
0.3703	0.3726	0.3828	0.3803	0.3784	0.3647	0.367	0.3578
0.3828	0.3803	0.3952	0.388	0.3898	0.3716	0.3784	0.3647
0.3871	0.3959	0.4006	0.4044	0.3952	0.388	0.3828	0.3803

Color Bin Structure



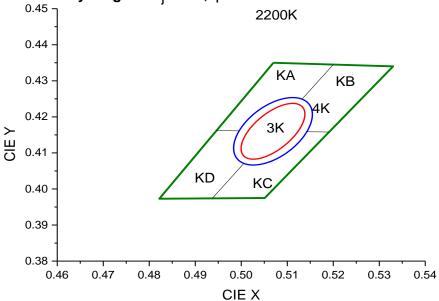
3500	K 3Step	3000	K 3Step	2700	K 3Step	
3	Step	3 Step		3 Step		
Center point	0.4073 : 0.3917	Center point	0.4338 : 0.4030	Center point	0.4578 : 0.4101	
Major Axis a	0.00927	Major Axis a	0.00834	Major Axis a	0.00810	
Minor Axis b	0.00414	Minor Axis b	0.00408	Minor Axis b	0.00420	
Ellipse	54.00	Ellipse	53.22	Ellipse	53.70	
Rotation Angle	34.00	Rotation Angle	tation Angle		55.70	

3500K 4Step		3000K 4Step		2700K 4Step	
4	Step	4 Step		4 Step	
Center point	0.4073 : 0.3917	Center point	0.4338 : 0.4030	Center point	0.4578 : 0.4101
Major Axis a	0.01236	Major Axis a	0.01112	Major Axis a	0.01080
Minor Axis b	0.00552	Minor Axis b	0.00544	Minor Axis b	0.00560
Ellipse	54.00	Ellipse	53.22	Ellipse	53.70
Rotation Angle	54.00	Rotation Angle	55.22	Rotation Angle	55.70

F	A	F	В	F	С	F	D
CIE X	CIE Y						
0.3996	0.4015	0.4146	0.4089	0.4082	0.392	0.3943	0.3853
0.3943	0.3853	0.4082	0.392	0.4017	0.3751	0.3889	0.369
0.4082	0.392	0.4223	0.399	0.4147	0.3814	0.4017	0.3751
0.4146	0.4089	0.4299	0.4165	0.4223	0.399	0.4082	0.392
G	A	G	В	G	c	G	D
CIE X	CIE Y						
0.4299	0.4165	0.443	0.4212	0.4345	0.4033	0.4223	0.399
0.4223	0.399	0.4345	0.4033	0.4259	0.3853	0.4147	0.3814
0.4345	0.4033	0.4468	0.4077	0.4373	0.3893	0.4259	0.3853
0.443	0.4212	0.4562	0.426	0.4468	0.4077	0.4345	0.4033
Н	IA	Н	В	н	c	Н	D
CIE X	CIE Y						
0.4562	0.426	0.4687	0.4289	0.4585	0.4104	0.4468	0.4077
0.4468	0.4077	0.4585	0.4104	0.4483	0.3919	0.4373	0.3893
0.4585	0.4104	0.4703	0.4132	0.4593	0.3944	0.4483	0.3919
0.4687	0.4289	0.481	0.4319	0.4703	0.4132	0.4585	0.4104

Color Bin Structure

CIE Chromaticity Diagram T_j =25 °C, I_F =65mA



2200K 3Step

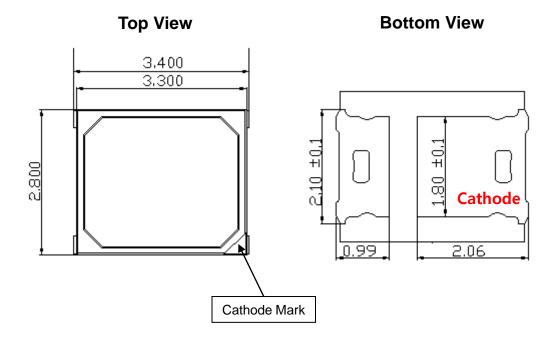
ZZOUK SSIEP						
3 Step						
Center point	0.5069 : 0.4160					
Major Axis a	0.00936					
Minor Axis b	0.0045					
Ellipse	50					
Rotation Angle	30					

2200K 4Step

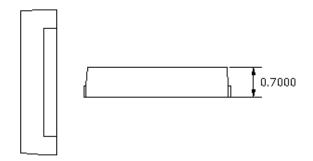
4 Step						
Center point	0.5069 : 0.4160					
Major Axis a	0.011					
Minor Axis b	0.0063					
Ellipse Rotation Angle	50					

K	Α	K	В	K	С	K	D
CIE X	CIE Y						
0.5070	0.4350	0.5200	0.4345	0.5069	0.4160	0.4946	0.4162
0.5200	0.4345	0.5330	0.4340	0.5191	0.4158	0.5069	0.4160
0.5069	0.4160	0.5191	0.4158	0.5051	0.3975	0.4937	0.3974
0.4946	0.4162	0.5069	0.4160	0.4937	0.3974	0.4822	0.3973

Mechanical Dimensions



Side View



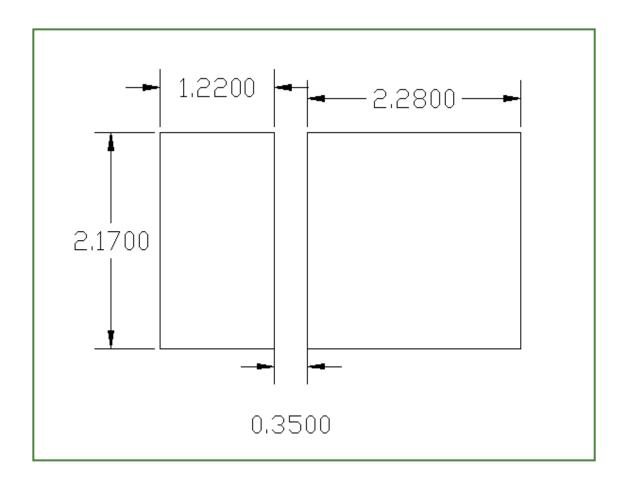
Notes:

(1) All dimensions are in millimeters.

(2) Scale: none

(3) Undefined tolerance is $\pm 0.2 mm$

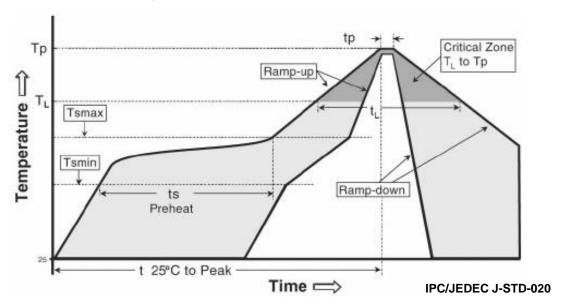
Recommended Solder Pad



Notes:

- (1) All dimensions are in millimeters.
- (2) Scale: none
- (3) This drawing without tolerances are for reference only
- (4) Undefined tolerance is ± 0.1 mm
- (5) The appearance and specifications of the product may be changed for improvement without notice.

Reflow Soldering Characteristics



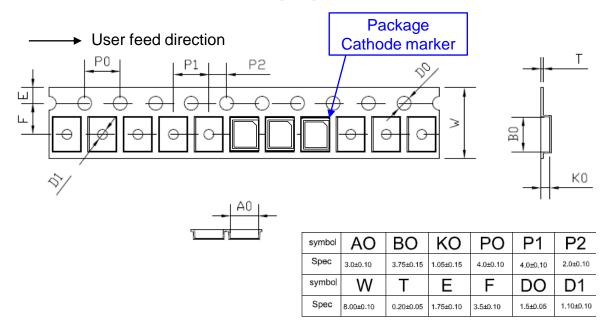
Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T _{s_max} to T _p)	3° C/second max.	3° C/second max.
$ \begin{array}{c} \textbf{Preheat} \\ \textbf{- Temperature Min } (\textbf{T}_{\text{S_min}}) \\ \textbf{- Temperature Max } (\textbf{T}_{\text{S_max}}) \\ \textbf{- Time } (\textbf{T}_{\text{S_min}} \ \text{to } \textbf{T}_{\text{S_max}}) \ (\textbf{t}_{\text{S}}) \\ \end{array} $	100 °C 150 °C 60-120 seconds	150 °C 200 °C 60-180 seconds
Time maintained above: - Temperature (T _L) - Time (t _L)	183 °C 60-150 seconds	217 °C 60-150 seconds
Peak Temperature (T _p)	215 ℃	260 ℃
Time within 5°C of actual Peak Temperature (t _p)2	10-30 seconds	20-40 seconds
Ramp-down Rate	6 °C/second max.	6 °C/second max.
Time 25°C to Peak Temperature	6 minutes max.	8 minutes max.

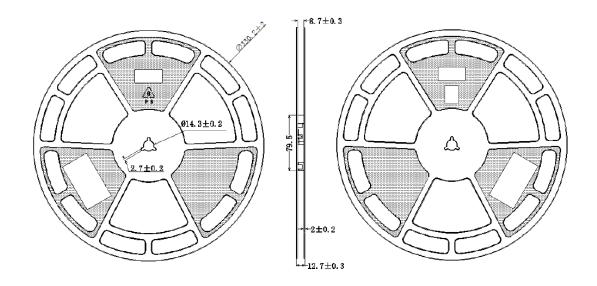
Caution:

- (1) Reflow soldering is recommended not to be done more than two times
 In the case of more than 24 hours passed soldering after first, LEDs will be damaged.
- (2) Repairs should not be done after the LEDs have been soldered When repair is unavoidable, suitable tools must be used.
- (3) Die slug is to be soldered.
- (4) When soldering, do not put stress on the LEDs during heating.
- (5) After soldering, do not warp the circuit board.



Emitter Tape & Reel Packaging



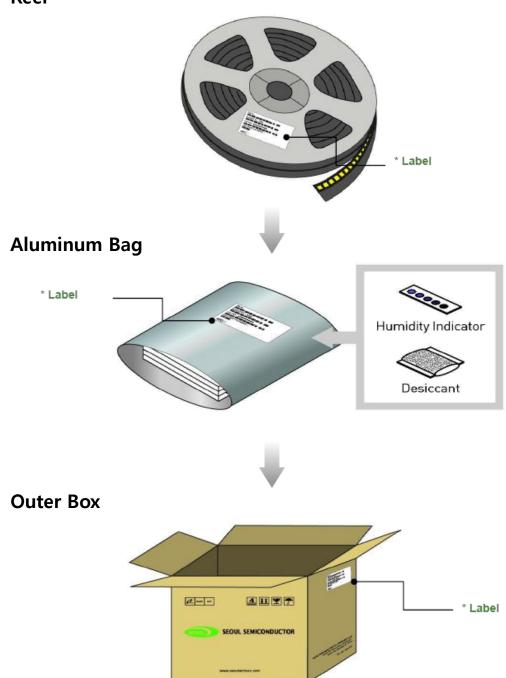


Notes:

- (1) Quantity: Max 16,000pcs/Reel
- (2) Cumulative Tolerance : Cumulative Tolerance/10 pitches to be ± 0.2 mm
- (3) Adhesion Strength of Cover Tape
 Adhesion strength to be 0.1-0.7N when the cover tape is turned off from the carrier tape at the angle of 10° to the carrier tape.
- (4) Package: P/N, Manufacturing data Code No. and Quantity to be indicated on a damp proof Package.

Emitter Tape & Reel Packaging

Reel



Product Nomenclature

Table 7. Part Numbering System

Part Number Code	Description	Part Number	Value
X ₁	Company	S	Seoul Semiconductor
X ₂	Level of Integration	1	Discrete LED
X ₃ X ₄	Technology	Wo	General White
$X_5X_6X_7X_8$	Dimension	2835	
X ₉ X ₁₀	ССТ	xx	
X ₁₁ X ₁₂	CRI	80	
X ₁₃ X ₁₄	Vf	03	
X ₁₅ X ₁₆ X ₁₇	Characteristic code Flux Rank	000	
X ₁₈ X ₁₉ X ₂₀	Characteristic code Vf Rank	000	
X ₂₁ X ₂₂	Characteristic code Color Step	00	
X ₂₃ X ₂₄	Туре	0P	
X ₂₅ X ₂₆ X ₂₇	Internal code	006	

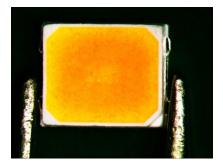


Handling of Silicone Resin for LEDs

(1) During processing, mechanical stress on the surface should be minimized as much as possible. Sharp objects of all types should not be used to pierce the sealing compound.



(2) In general, LEDs should only be handled from the side. By the way, this also applies to LEDs without a silicone sealant, since the surface can also become scratched.



- (3) When populating boards in SMT production, there are basically no restrictions regarding the form of the pick and place nozzle, except that mechanical pressure on the surface of the resin must be prevented. This is assured by choosing a pick and place nozzle which is larger than the LED's reflector area.
- (4) Silicone differs from materials conventionally used for the manufacturing of LEDs. These conditions must be considered during the handling of such devices. Compared to standard encapsulants, silicone is generally softer, and the surface is more likely to attract dust.

As mentioned previously, the increased sensitivity to dust requires special care during processing. In cases where a minimal level of dirt and dust particles cannot be guaranteed, a suitable cleaning solution must be applied to the surface after the soldering of components.

- (5) SSC suggests using isopropyl alcohol for cleaning. In case other solvents are used, it must be assured that these solvents do not dissolve the package or resin.

 Ultrasonic cleaning is not recommended. Ultrasonic cleaning may cause damage to the LED.
- (6) Please do not mold this product into another resin (epoxy, urethane, etc) and do not handle this. product with acid or sulfur material in sealed space.



Precaution for Use

(1) Storage

To avoid the moisture penetration, we recommend store in a dry box with a desiccant.

The maximum storage temperature range is 40° C and a maximum humidity of RH90%.

(2) Use Precaution after Opening the Packaging

Use SMT techniques properly when the LED is to be soldered dipped as separation of the lens m ay affect the light output efficiency.

Pay attention to the following:

- a. Recommend conditions after opening the package
 - Sealing
 - Temperature : 30°C Humidity : less than RH60%
- b. If the package has been opened more than 4 week(MSL_2a) or the color of the desiccant changes, components should be dried for 10-24hr at $65\pm5^{\circ}$ C
- (3) Do not apply mechanical force or excess vibration during the cooling process to normal temperature after soldering.
- (4) Do not rapidly cool device after soldering.
- (5) Components should not be mounted on warped (non coplanar) portion of PCB.
- (6) Radioactive exposure is not considered for the products listed here in.
- (7) Gallium arsenide is used in some of the products listed in this publication.
 These products are dangerous if they are burned or shredded in the process of disposal.
 It is also dangerous to drink the liquid or inhale the gas generated by such products when chemically disposed of.
- (8) This device should not be used in any type of fluid such as water, oil, organic solvent and etc. When washing is required, IPA (Isopropyl Alcohol) should be used.
- (9) When the LEDs are in operation the maximum current should be decided after measuring the package temperature.

Precaution for Use

- (10) The appearance and specifications of the product may be modified for improvement without notice.
- (11) Long time exposure of sunlight or occasional UV exposure will cause lens discoloration.
- (12) VOCs (Volatile organic compounds) emitted from materials used in the construction of fixtures can penetrate silicone encapsulants of LEDs and discolor when exposed to heat and photonic energy. The result can be a significant loss of light output from the fixture. Knowledge of the properties of the materials selected to be used in the construction of fixtures can help prevent these issues.
- (13) Attaching LEDs, do not use adhesives that outgas organic vapor.
- (14) The driving circuit must be designed to allow forward voltage only when it is ON or OFF.
 If the reverse voltage is applied to LED, migration can be generated resulting in LED damage.
- (15) Similar to most Solid state devices;
 LEDs are sensitive to Electro-Static Discharge (ESD) and Electrical Over Stress (EOS).
 Below is a list of suggestions that Seoul Semiconductor purposes to minimize these effects.
- a. ESD (Electro Static Discharge)

Electrostatic discharge (ESD) is the defined as the release of static electricity when two objects come into contact. While most ESD events are considered harmless, it can be an expensive problem in many industrial environments during production and storage. The damage from ESD to an LEDs may cause the product to demonstrate unusual characteristics such as:

- Increase in reverse leakage current lowered turn-on voltage
- Abnormal emissions from the LED at low current

The following recommendations are suggested to help minimize the potential for an ESD event. One or more recommended work area suggestions:

- Ionizing fan setup
- ESD table/shelf mat made of conductive materials
- ESD safe storage containers

One or more personnel suggestion options:

- Antistatic wrist-strap
- Antistatic material shoes
- Antistatic clothes

Environmental controls:

- Humidity control (ESD gets worse in a dry environment)



Precaution for Use

b. EOS (Electrical Over Stress)

Electrical Over-Stress (EOS) is defined as damage that may occur when an electronic device is subjected to a current or voltage that is beyond the maximum specification limits of the device. The effects from an EOS event can be noticed through product performance like:

- Changes to the performance of the LED package
 (If the damage is around the bond pad area and since the package is completely encapsulated the package may turn on but flicker show severe performance degradation.)
- Changes to the light output of the luminaire from component failure
- Components on the board not operating at determined drive power

Failure of performance from entire fixture due to changes in circuit voltage and current across total circuit causing trickle down failures. It is impossible to predict the failure mode of every LED exposed to electrical overstress as the failure modes have been investigated to vary, but there are some common signs that will indicate an EOS event has occurred:

- Damaged may be noticed to the bond wires (appearing similar to a blown fuse)
- Damage to the bond pads located on the emission surface of the LED package (shadowing can be noticed around the bond pads while viewing through a microscope)
- Anomalies noticed in the encapsulation and phosphor around the bond wires.
- This damage usually appears due to the thermal stress produced during the EOS event.
- c. To help minimize the damage from an EOS event Seoul Semiconductor recommends utilizing:
 - A surge protection circuit
 - An appropriately rated over voltage protection device
 - A current limiting device



Company Information

Published by

Seoul Semiconductor © 2013 All Rights Reserved.

Company Information

Seoul Semiconductor (www.SeoulSemicon.com) manufacturers and packages a wide selection of light emitting diodes (LEDs) for the automotive, general illumination/lighting, Home appliance, signage and back lighting markets. The company is the world's fifth largest LED supplier, holding more than 10,000 patents globally, while offering a wide range of LED technology and production capacity in areas such as "nPola", "Acrich", the world's first commercially produced AC LED, and "Acrich MJT - Multi-Junction Technology" a proprietary family of high-voltage LEDs.

The company's broad product portfolio includes a wide array of package and device choices such as Acrich and Acirch2, high-brightness LEDs, mid-power LEDs, side-view LEDs, and through-hole type LEDs as well as custom modules, displays, and sensors.

Legal Disclaimer

Information in this document is provided in connection with Seoul Semiconductor products. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Seoul Semiconductor hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party. The appearance and specifications of the product can be changed to improve the quality and/or performance without notice.